



# **ZXTN2038F** SOT23 80 volt NPN silicon planar medium power transistor

## Summary

 $V_{(BR)CEV} > 80V$  $V_{(BR)CEO} > 60V$  $I_{c(cont)} = 1A$ V<sub>ce(sat)</sub> < 500mV @ 1A

### **Complementary type**

ZXTP2039F

## Description

This transistor combines high gain, high current operation and low saturation voltage making it ideal for power MOSFET gate driving and low loss power switching.

### Features

- · Low saturation voltage for reduced power dissipation
- 1 to 2 amp high current capability
- · Pb-free
- SOT23 package

## **Applications**

- Power MOSFET gate driving
- Low loss power switching

## **Ordering information**

Device	vice Reel size		Quantity per reel	
ZXTN2038FTA	7″	8mm	3,000	
ZXTN2038FTC	13″	8mm	10,000	

### **Device marking**

N38

## Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V <sub>CBO</sub>	80	V
Collector-emitter voltage	V <sub>CEV</sub>	80	V
Collector-emitter voltage	V <sub>CEO</sub>	60	V
Emitter-base voltage	V <sub>EBO</sub>	5.0	V
Peak pulse current	I <sub>CM</sub>	2	А
Continuous collector current <sup>(*)</sup>	I <sub>C</sub>	1	А
Peak base current	I <sub>BM</sub>	1	А
Power dissipation @ T <sub>A</sub> =25°C <sup>(*)</sup>	P <sub>D</sub>	350	mW
Operating and storage temperature	T <sub>j</sub> :T <sub>stg</sub>	55 to +150	°C

NOTES:

(\*) For a device surface mounted on a 15mm x 15mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

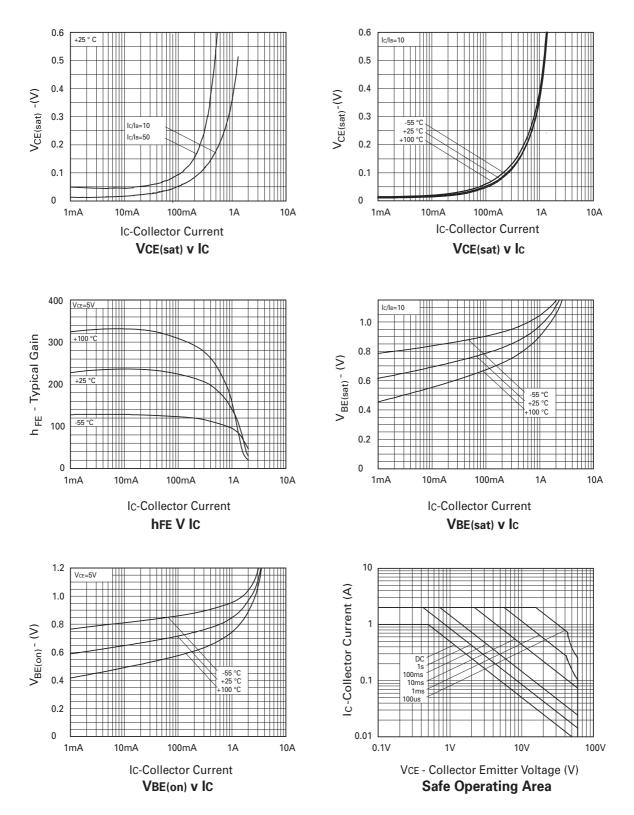
## Electrical characteristics (@ $T_{AMB} = 25^{\circ}C$ )

Parameter	Symbol	Min.	Max.	Unit	Conditions
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	80		V	Ι <sub>C</sub> =100μΑ
Collector-emitter breakdown voltage	V <sub>(BR)CEV</sub>	80		V	I <sub>C</sub> =100μA, 0.3V > V <sub>BE</sub> > -1V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	60		V	I <sub>C</sub> =10mA <sup>(*)</sup>
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	5		V	I <sub>E</sub> =100μA
Collector-emitter cut-off current	I <sub>CES</sub>		100	nA	V <sub>CE</sub> =60V
Collector-base cut-off current	I <sub>CBO</sub>		100	nA	V <sub>CB</sub> =60V
Emitter-base cut-off current	I <sub>EBO</sub>		100	nA	V <sub>EB</sub> =4V
Static forward current transfer ratio	h <sub>FE</sub>	100 100 80 30	300		$I_{C}=1mA, V_{CE}=5V$ $I_{C}=500mA, V_{CE}=5V^{(*)}$ $I_{C}=1A, V_{CE}=5V^{(*)}$ $I_{C}=2A, V_{CE}=5V^{(*)}$
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>		0.2 0.25 0.5	V V V	$I_{C}=100mA, I_{B}=2mA^{(*)}$ $I_{C}=500mA,$ $I_{B}=50mA^{(*)}$ $I_{C}=1A, I_{B}=100mA^{(*)}$
Base-emitter saturation voltage	V <sub>BE(sat)</sub>		1.1	V	I <sub>C</sub> =1A, I <sub>B</sub> =100mA <sup>(*)</sup>
Base-emitter turn-on voltage	V <sub>BE(on)</sub>		1.0	V	I <sub>C</sub> =1A, V <sub>CE</sub> =5V <sup>(*)</sup>
Transition frequency	f <sub>T</sub>	150			I <sub>C</sub> =50mA, V <sub>CE</sub> =10V f=100MHz
Output capacitance	C <sub>obo</sub>		10	pF	V <sub>CB</sub> =10V, f=1MHz

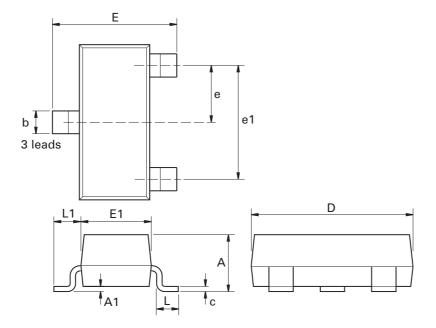
### NOTES:

(\*) Measured under pulsed conditions. Pulse width=300 $\mu S.$  Duty cycle  ${\leq}2\%$  Spice parameter data is available upon request for this device

## **Typical characteristics**



## Packaging details - SOT23



## Package dimensions

Dim.	Millin	neters	Inc	hes	Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
А	-	1.12	-	0.044	e1	1.90 NOM		0.075 NOM	
A1	0.01	0.10	0.0004	0.004	E	2.10	2.64	0.083	0.104
b	0.30	0.50	0.012	0.020	E1	1.20	1.40	0.047	0.055
с	0.085	0.20	0.003	0.008	L	0.25	0.60	0.0098	0.0236
D	2.80	3.04	0.110	0.120	L1	0.45	0.62	0.018	0.024
е	0.95	NOM	0.037	NOM	-			-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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